

Low-Noise Bias Supply in μ MAX with Power-OK for GaAsFET PA

ABSOLUTE MAXIMUM RATINGS

IN to GND-0.3V to +6V
 $\overline{\text{SHDN}}$ to GND-0.3V to +6V
 $\overline{\text{POK}}$ to GND-0.3V to +12V
 C1+ to GND-0.3V to ($V_{\text{IN}} + 0.3\text{V}$)
 C1-, NEGOUT, OUT, FB to GND-6V to ($V_{\text{IN}} + 0.3\text{V}$)
 Continuous Power Dissipation ($T_A = +70^\circ\text{C}$)
 10-Pin μ MAX (derate 5.6mW/ $^\circ\text{C}$ above $+70^\circ\text{C}$)444mW

Operating Temperature Range-40 $^\circ\text{C}$ to +85 $^\circ\text{C}$
 Junction Temperature+150 $^\circ\text{C}$
 Storage Temperature Range-65 $^\circ\text{C}$ to +165 $^\circ\text{C}$
 Lead Temperature (soldering, 10s)+300 $^\circ\text{C}$

Note 1: The output may be shorted to NEGOUT or GND if the package power dissipation is not exceeded. Typical short-circuit current is 35mA.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 3, $V_{\text{IN}} = +3.6\text{V}$, FB = GND, $R_L = \infty$, $\overline{\text{SHDN}} = \text{IN}$, $T_A = -40^\circ\text{C}$ to +85 $^\circ\text{C}$, unless otherwise noted. Typical values are at $T_A = +25^\circ\text{C}$.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Supply Voltage Range	V _{IN}			2.5		5.5	V
Preset Output Voltage	V _{OUT}	V _{IN} ≥ 2.7V, I _{OUT} = 0 to 4mA		-2.1	-2.0	-1.9	V
Adjustable Output Voltage Range	V _{OUT}	V _{IN} ≥ 2.5V, I _{OUT} = 0 to 4mA		-(V _{IN} - 0.6)		-0.5	V
FB Voltage	V _{FB}	V _{IN} ≥ 2.5V, I _{OUT} = 0 to 4mA	T _A = +25°C	-0.515	-0.5	-0.485	V
			T _A = 0°C to +85°C	-0.525		-0.475	
			T _A = -40°C to +85°C	-0.535		-0.465	
FB Input Current		V _{FB} = -0.5V			-10	-100	nA
Supply Current (Note 3)	I _Q				500	950	μA
Shutdown Supply Current	I _{SHUT}	SHDN = GND			0.05	1	μA
Output Load Regulation		V _{IN} ≥ 2.7V, I _{OUT} = 0 to 4mA			2	6	mV/mA
Output Ripple		I _{OUT} = 4mA, circuit of Figure 3b			1		mVp-p
Oscillator Frequency	f _{OSC}			80	100	120	kHz
POK Threshold		FB = OUT		90	92.5	95	% of V _{OUT}
POK Output Level		V _{IN} ≥ 2.5V, sinking 1mA				100	mV
POK Off Leakage Current		V _{POK} = 11V				1	μA
SHDN Input High Voltage	V _{IH}	V _{IN} = 5.5V		2.2			V
SHDN Input Low Voltage	V _{IL}	V _{IN} = 2.5V				0.35	V
SHDN Input Current	I _{SHDN}	Connected to IN or GND				±1	μA
SHDN Input Capacitance	C _{IN}				10		pF
Startup Time	t _{START}	V _{IN} = 3V, R _L = 500Ω, V _{SHDN} = 0 to V _{IN} , POK goes low				1	ms

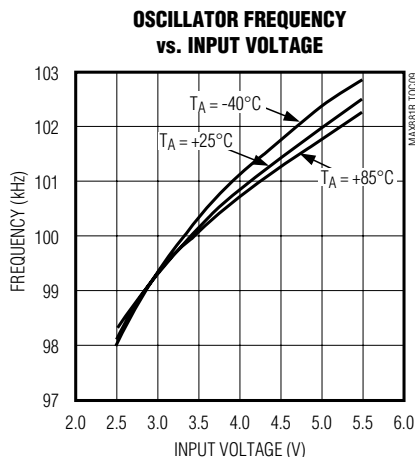
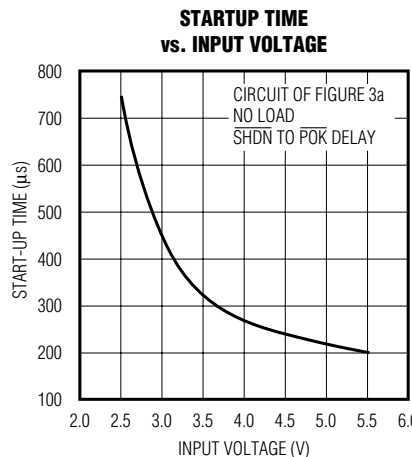
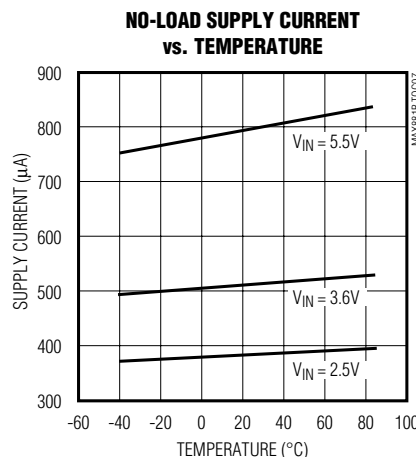
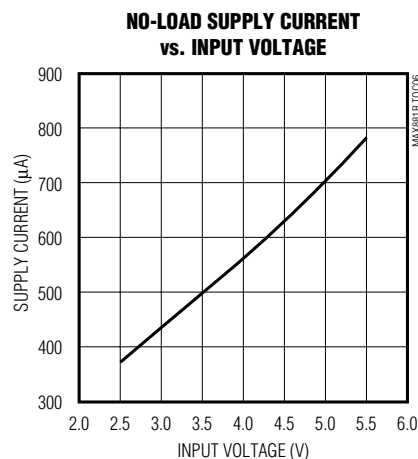
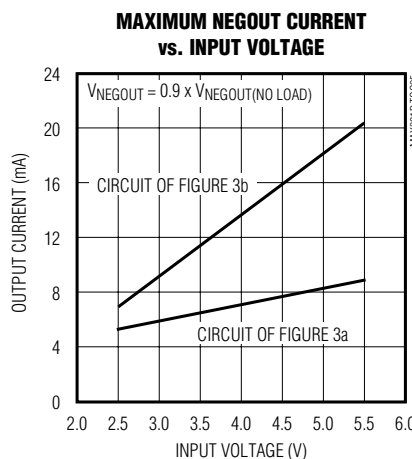
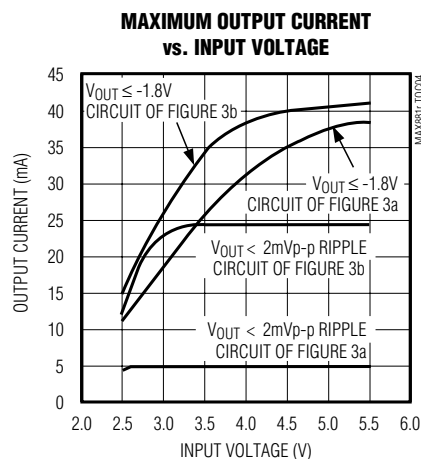
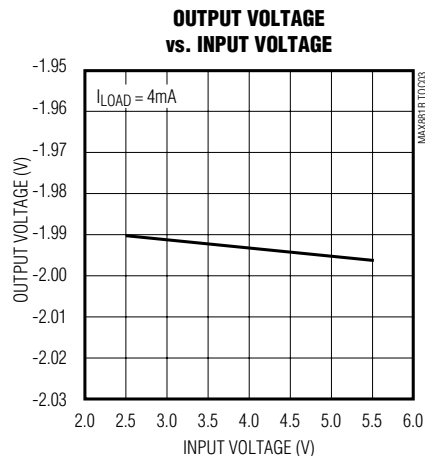
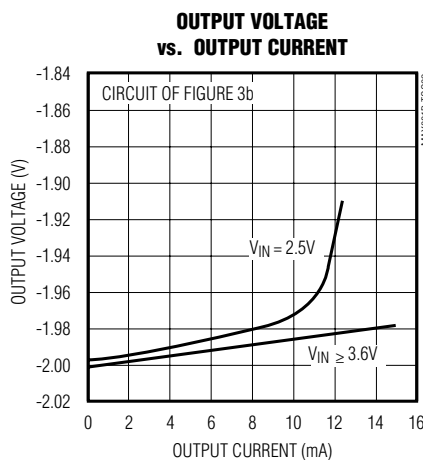
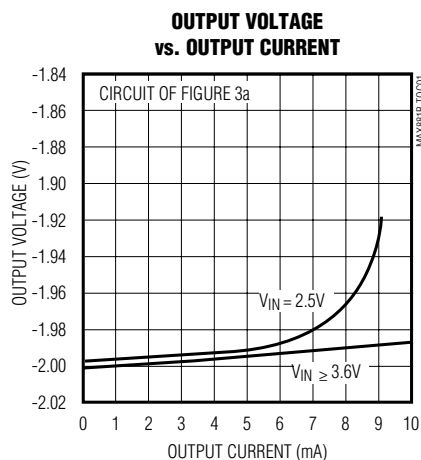
Note 2: Specifications to -40 $^\circ\text{C}$ are guaranteed by design, not production tested.

Note 3: MAX881R may draw high supply current during startup, up to the minimum operating supply voltage. To guarantee proper startup, the input supply must be capable of delivering 90mA more than the maximum load current.

Low-Noise Bias Supply in μ MAX with Power-OK for GaAsFET PA

Typical Operating Characteristics

(Circuit of Figure 3, $V_{IN} = 3.6V$, $T_A = +25^\circ C$, unless otherwise noted.)

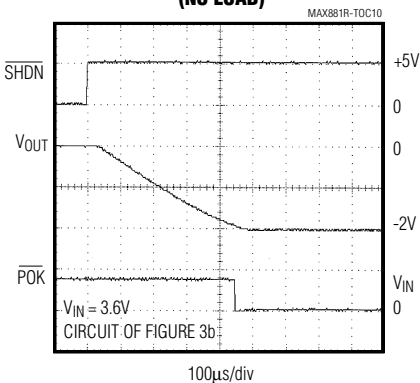


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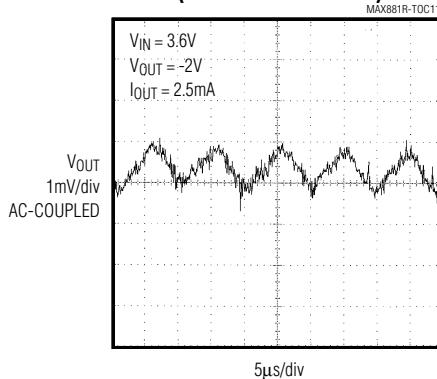
Typical Operating Characteristics (continued)

(Circuit of Figure 3, $V_{IN} = 3.6V$, $T_A = +25^\circ C$, unless otherwise noted.)

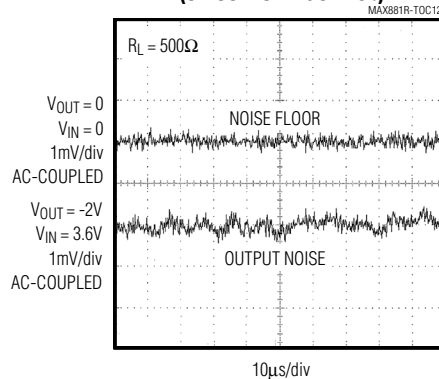
**STARTUP FROM SHUTDOWN
(NO LOAD)**



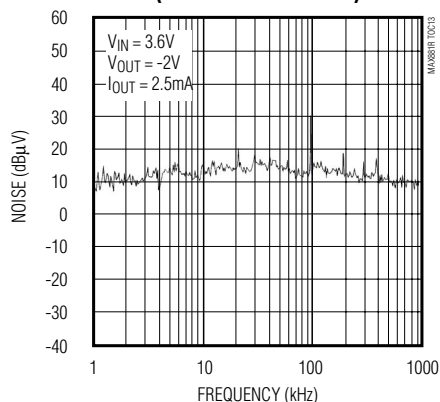
**OUTPUT NOISE AND RIPPLE
(CIRCUIT OF FIGURE 3a)**



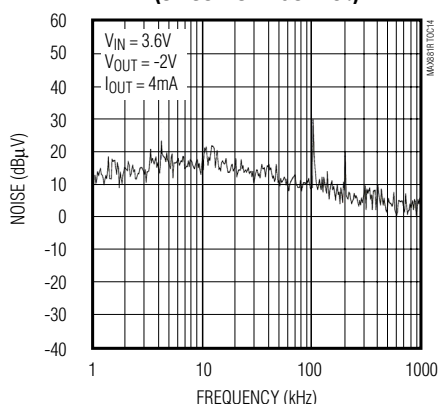
**OUTPUT NOISE AND RIPPLE
(CIRCUIT OF FIGURE 3b)**



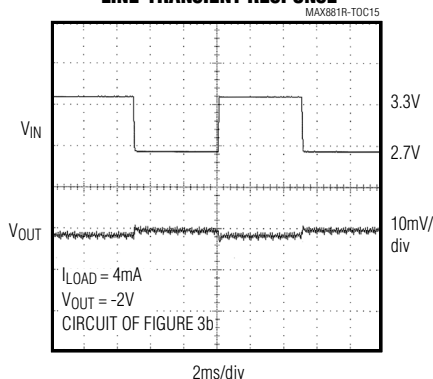
**OUTPUT NOISE SPECTRUM
(CIRCUIT OF FIGURE 3a)**



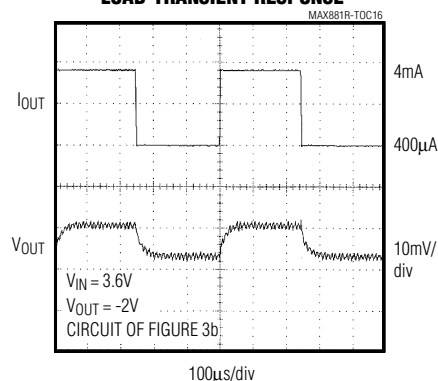
**OUTPUT NOISE SPECTRUM
(CIRCUIT OF FIGURE 3b)**



LINE-TRANSIENT RESPONSE



LOAD-TRANSIENT RESPONSE



Low-Noise Bias Supply in μ MAX with Power-OK for GaAsFET PA

MAX881R

Pin Description

PIN	NAME	FUNCTION
1	C1+	Positive Terminal for C1
2	C1-	Negative Terminal for C1
3	NEGOUT	Negative Output Voltage (unregulated)
4	$\overline{\text{POK}}$	Active-Low, Open-Drain Power-OK Output. Goes low when OUT reaches 92.5% of its set value.
5	$\overline{\text{SHDN}}$	Active-Low, Logic-Level Shutdown Input. Connect to IN for normal operation. Do not leave this pin unconnected.
6	FB	Dual-Mode™ Feedback Input. When FB is connected to GND, the output is preset to -2V. To select other voltages, connect FB to an external resistor-divider (Figure 4). Do not leave this pin unconnected.
7	OUT	Regulated Negative Output Voltage
8	GND	Ground
9	N.C.	No Connection. Not internally connected.
10	IN	Positive Power-Supply Input

Dual Mode is a trademark of Maxim Integrated Products.

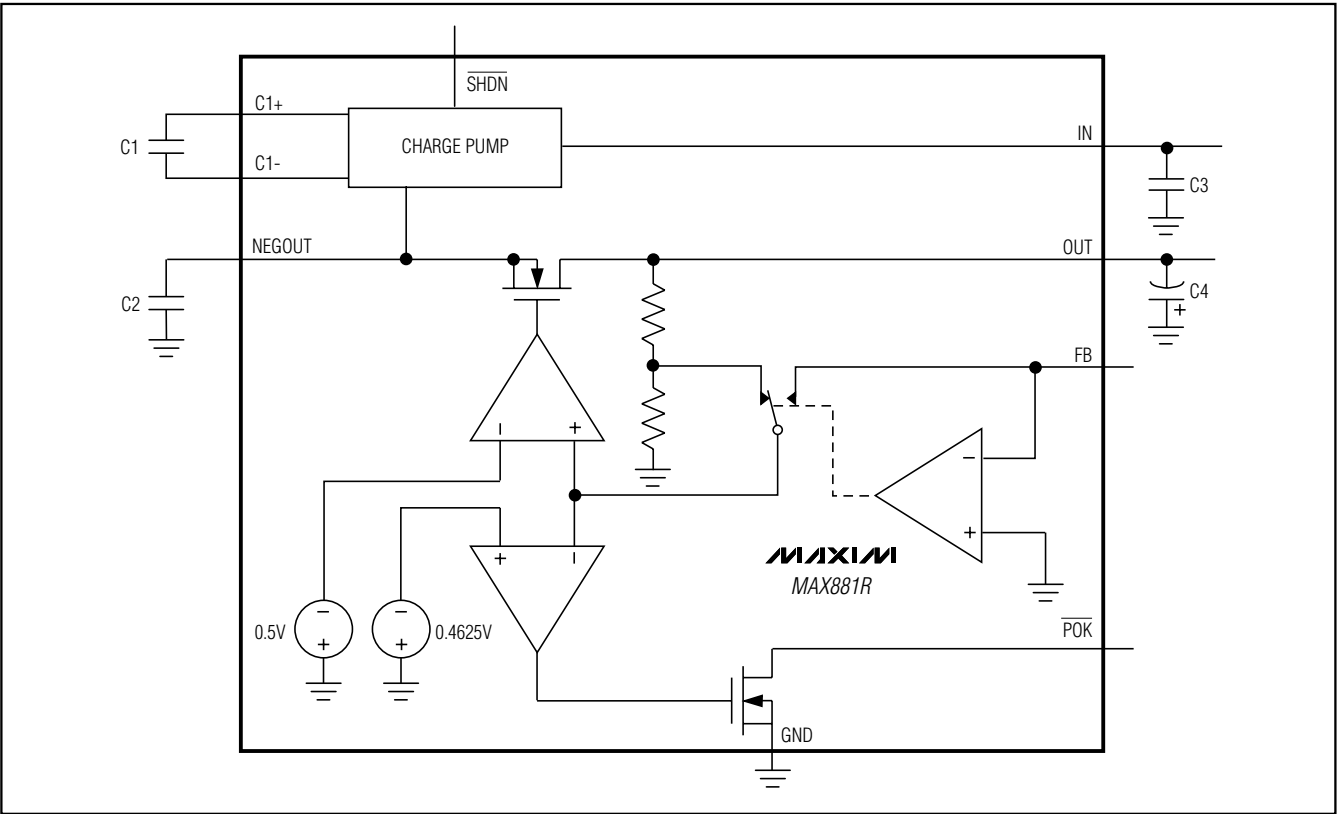


Figure 1. Functional Diagram

Low-Noise Bias Supply in μ MAX with Power-OK for GaAsFET PA

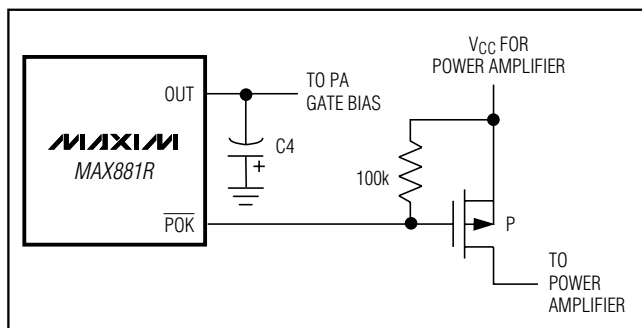


Figure 2. Using the $\overline{\text{POK}}$ Function

Detailed Description

The MAX881R, a low-noise, inverting, regulated charge-pump power supply, is designed for biasing GaAsFET devices such as power-amplifier modules in cellular handsets.

The applied input voltage (V_{IN}) is inverted to a negative voltage at NEGOUT by a capacitive pump. This voltage is regulated by an internal linear regulator at OUT (Figure 1). With FB connected to GND, V_{OUT} is regulated at -2V. Alternatively, use a voltage-divider at FB to adjust the output voltage between -0.5V and $-(V_{\text{IN}} - 0.6\text{V})$ (see the section *Setting the Output Voltage*). The internal linear regulator reduces the ripple noise induced by the charge-pump inverter to 1mVp-p at OUT (circuit of Figure 3b). In addition, the excellent AC rejection of the linear regulator attenuates noise from the incoming supply.

Power-OK Signal

The MAX881R has an active-low, open-drain, power-OK (POK) output. This output goes low when OUT reaches 92.5% of the regulated output voltage. $\overline{\text{POK}}$ can be used to drive the gate of a P-MOSFET that switches power to the GaAsFET power amplifier (Figure 2), thereby ensuring that the power amplifier is not powered before the required negative bias voltage is present.

Use a 50k Ω or larger pull-up resistor to signal a logic high when POK goes high impedance.

Shutdown Mode

The MAX881R features a shutdown mode that reduces supply current to less than 1 μ A over temperature. SHDN is an active-low, logic-level input. Start-up time coming out of shutdown mode is typically 0.5ms. OUT and NEGOUT are switched to GND in shutdown mode.

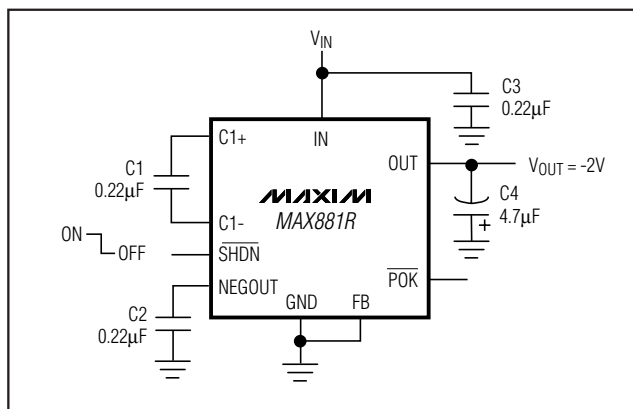


Figure 3a. Standard Application Circuit for Minimum Capacitor Values

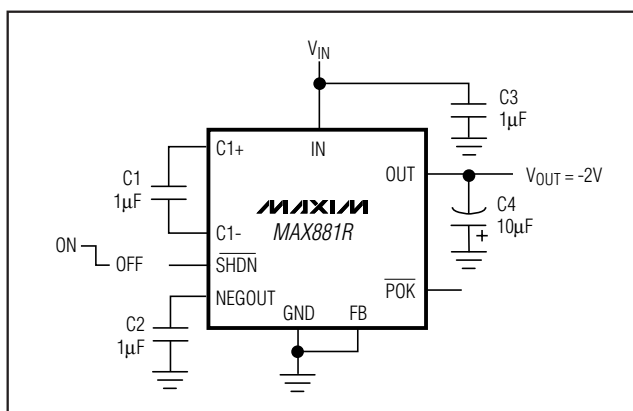


Figure 3b. Standard Application Circuit for Minimum Output Noise

Applications Information

Setting the Output Voltage

Select either a fixed or adjustable output for the MAX881R. Connect FB to GND for a fixed -2V output (Figure 3). Select an alternative output voltage by connecting FB to the midpoint of a resistor-divider from OUT to GND (Figure 4). When operating under full load (4mA), the voltage at IN should be at least 0.6V higher than the absolute voltage required at OUT. Note that the minimum input voltage required for operation is 2.5V, regardless of the desired output voltage. Choose R1 to be between 100k Ω and 400k Ω and calculate R2. For greater accuracy, use resistors with 1% or better tolerance.

$$R2 = R1 (2 \times |V_{\text{OUT}}| - 1)$$

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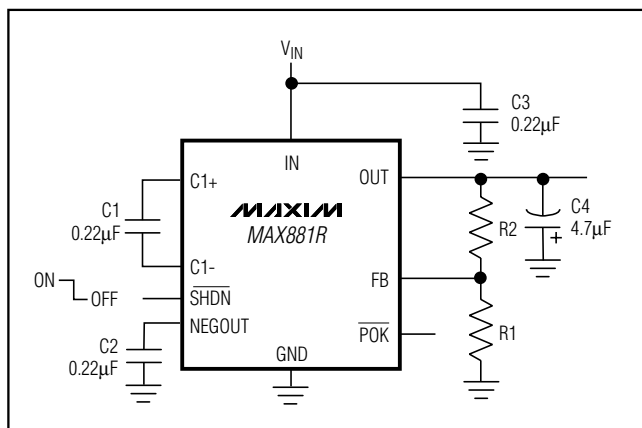


Figure 4. Adjustable Output Configuration

Capacitors

Use capacitors with a low effective series resistance (ESR) to maintain a low dropout voltage ($V_{IN} - IV_{OUT}$). The overall dropout voltage is a function of the output resistance of the charge pump and the voltage drop across the linear regulator (N-channel pass transistor). At the 100kHz charge-pump switching frequency, output resistance is a function of the value of C1 and the ESR of C1 and C2. Therefore, increasing C1 and minimizing the ESR of the charge-pump capacitors minimizes dropout voltage.

The output resistance of the entire circuit (in dropout) is approximately:

$$R_{OUT} = R_O + 4 \times ESR_{C1} + ESR_{C2} + 1 / (f_S \times C1) + R_{(linear\ regulator)}$$

Where $R_{(linear\ regulator)}$ (the output impedance of the linear regulator) is approximately 2Ω and R_O (the resistance of the internal switches) is typically 10Ω . When

regulating, the output resistance of the circuit is simply the linear-regulator load regulation ($2mV/mA$).

C1, C2, and C3 should be $0.22\mu F$ capacitors with less than 0.4Ω ESR. C4 should be a $4.7\mu F$ capacitor with less than 0.1Ω ESR. Larger capacitor values can be used ($C1 = C2 = C3 = 1\mu F$, $C4 = 10\mu F$) to reduce output noise and ripple ($1mVp-p$), at the expense of cost and board space. All capacitors should be either ceramic or surface-mount chip tantalum (Figures 3a and 3b).

Layout and Grounding

Good layout is important for good noise performance. To optimize the layout:

- 1) Mount all components as close together as possible.
- 2) Keep traces short to minimize parasitic inductance and capacitance, especially connections to FB.
- 3) Use a ground plane.

Noise and Ripple Measurement

Accurately measuring the output noise and ripple is a challenge. Slight momentary differences in ground potential between the circuit and the oscilloscope (which result from the charge pump's switching action) cause ground currents in the probes' wires, inducing sharp voltage spikes. For best results, measure directly across the output capacitor (C4). Do not use the ground lead of the probe; instead, remove the probe's tip cover and touch the ground ring on the probe directly to C4's ground terminal. This direct connection gives the most accurate noise and ripple measurement.

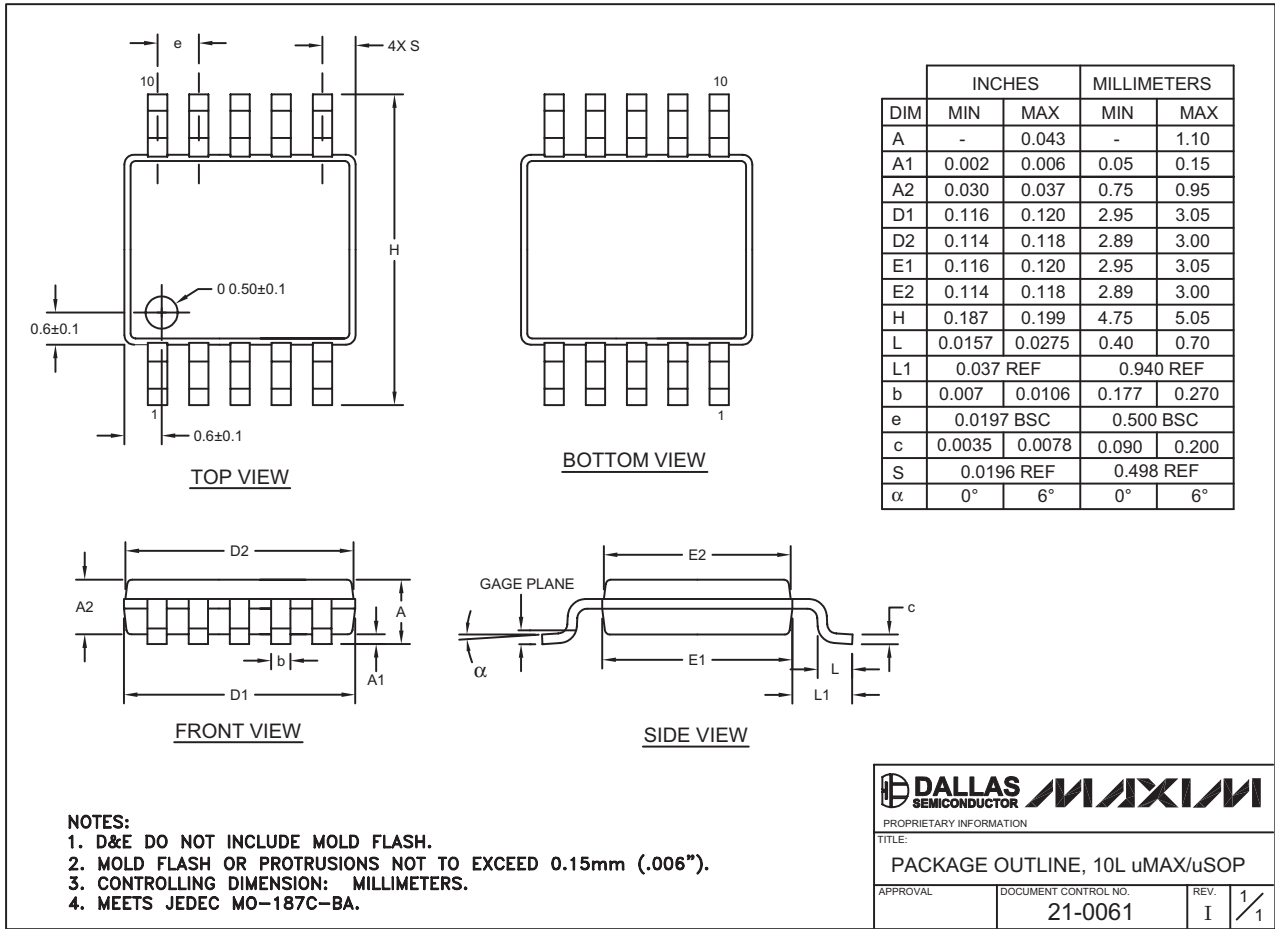
Chip Information

TRANSISTOR COUNT: 413

Low-Noise Bias Supply in μ MAX with Power-OK for GaAsFET PA

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)



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